ABSTRACT OF THE DISCLOSURE

The disclosure is provided with: a temporary crimping step in which one or more semiconductor chips are sequentially laminated while being temporarily crimped in each of two or more locations on a substrate to thereby form chip stacks in a temporarily crimped state; and a permanent crimping step in which the top surfaces of all of the chip stacks formed in the temporarily crimped state are sequentially heated, pressurized, and permanently crimped. Furthermore, a specifying step is provided prior to the temporary crimping step for specifying a separation distance which is the distance from the chip stacks under permanent crimping to a location at which the temperature of the substrate, the temperature having been raised by heating for the permanent crimping, becomes less than or equal to a prescribed permissible temperature.

FIGURE 7